



PNPN SILICON, REVERSE-BLOCKING, POWER TRIODE THYRISTORS

Qualified per MIL-PRF-19500/108

Qualified Levels:
JAN and JANTX

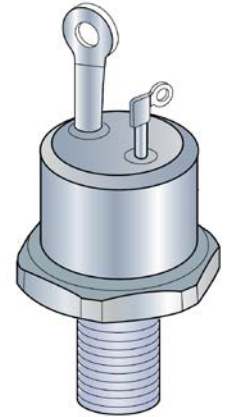
DESCRIPTION

This silicon controlled rectifier device is military qualified up to a JANTX level for high-reliability applications. Microsemi also offers numerous other products to meet higher and lower power voltage regulation applications.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N682, 2N683, 2N685, 2N687 – 2N692 and 2N5206.
- JAN and JANTX qualifications are available per MIL-PRF-19500/108.
- RoHS compliant versions available (commercial grade only).



**TO-208 / TO-48
Package**

APPLICATIONS / BENEFITS

- A general purpose, reverse-blocking thyristor.

MAXIMUM RATINGS

Parameters/Test Conditions	Symbol	Value	Unit
Junction Temperature	T_J	-65 to +125	°C
Storage Temperature	T_{STG}	-65 to +150	°C
Gate Voltage	V_{GM}	5	V(pk)
Maximum Average DC Output Current ⁽¹⁾	I_O	16	A
Non-repetitive Peak On-State Current ⁽²⁾ @ t = 7 ms	I_{TSM}	150	A

- Notes:**
1. This average forward current is for a maximum case temperature of +65 °C, and 180 electrical degrees of conduction.
 2. Surge rating is non-recurrent and applies only with device in the conducting state. The peak rate of surge current must not exceed 100 amperes during the first 10 μ s after switching from the off (blocking) state to the on (conducting) state. This time is measured from the point where the thyristor voltage has decayed to 90 percent of its initial blocking value.

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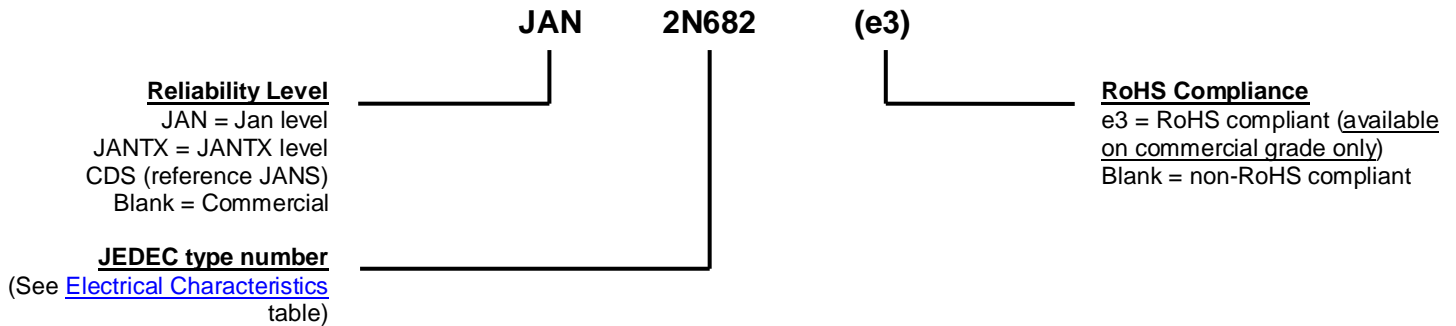
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MECHANICAL and PACKAGING

- CASE: Nickel plated copper.
- TERMINALS: Nickel plated steel, solder dipped.
- MARKING: Manufacturer's ID, part number, date code, polarity.
- POLARITY: Terminal 1: gate, terminal 2: cathode, terminal 3 (stud): anode.
- WEIGHT: 12.36 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

Symbol	Definition
V _{AA}	Anode power supply voltage (dc).

ELECTRICAL CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}^{(1)}$ and		50	V (pk)
2N682			100	
Repetitive peak off-state voltage	V_{DRM}		200	
2N683			250	
2N685			300	
2N686			400	
2N687			500	
2N688			600	
2N689			700	
2N690			800	
2N691			1,000	
2N692				
2N5206				

(1) Values applicable to zero or negative gate voltage (V_{GM}).

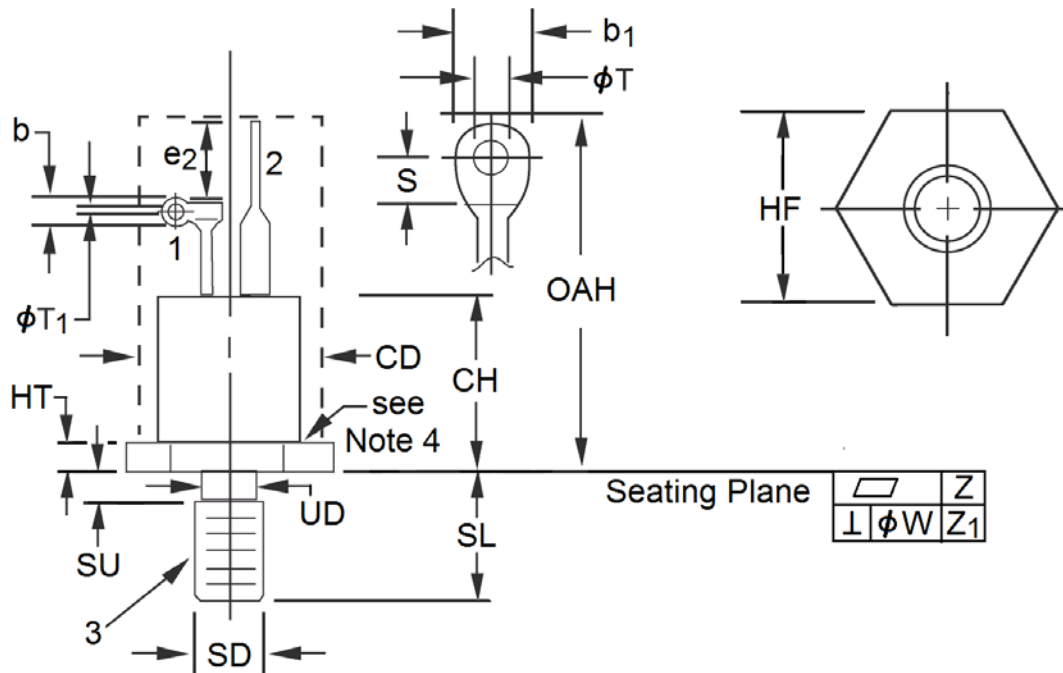
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Holding current: Bias condition D; $V_{AA} = 24$ V maximum; $I_{TM} = I_{F1} = 1$ A $I_T = I_{F2} = 100$ mA trigger voltage source = 10 V trigger PW = 100 μ s (minimum) $R_2 = 20$ Ω	I_H		50	mA
Reverse blocking current AC method, bias condition D; $f = 60$ Hz, $V_{RRM} = \text{rated}$	I_{RRM1}		2	mA (pk)
Forward blocking current AC method, bias condition D; $f = 60$ Hz, $V_{DRM} = \text{rated}$	I_{DRM1}		2	mA (pk)
Gate trigger voltage and current $V_2 = V_D = 6$ V; $R_L = 50$ Ω ; $R_e = 20$ Ω maximum	V_{GT1} I_{GT1}		3 35	V mA
Forward on voltage $I_{TM} = 50$ A(pk) (pulse); pulse width = 8.5 ms; maximum; duty cycle = 2 percent maximum	V_{TM}		2	V (pk)
Reverse gate current $V_G = 5$ V	I_G		250	mA

ELECTRICAL CHARACTERISTICS (continued)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Reverse blocking current ($T_C = +120\text{ }^\circ\text{C}$) AC method, bias condition D; $f = 60\text{ Hz}$; $V_{RRM} = \text{rated}$	I_{RRM2}		5	mA (pk)
Forward blocking current ($T_C = +120\text{ }^\circ\text{C}$) AC method, bias condition D; $f = 60\text{ Hz}$; $V_{DRM} = \text{rated}$	I_{DRM2}		5	mA (pk)
Gate trigger voltage ($T_C = +120\text{ }^\circ\text{C}$; $R_e = 20\text{ }\Omega$ max) <div style="display: flex; justify-content: space-between;"> <div style="width: 80%;"> $V_2 = V_{DM} = 50\text{ V}$; $R_L = 140\text{ }\Omega$ $V_2 = V_{DM} = 100\text{ V}$; $R_L = 140\text{ }\Omega$ $V_2 = V_{DM} = 200\text{ V}$; $R_L = 140\text{ }\Omega$ $V_2 = V_{DM} = 250\text{ V}$; $R_L = 650\text{ }\Omega$ $V_2 = V_{DM} = 300\text{ V}$; $R_L = 650\text{ }\Omega$ $V_2 = V_{DM} = 400\text{ V}$; $R_L = 3\text{ k}\Omega$ $V_2 = V_{DM} = 500\text{ V}$; $R_L = 3\text{ k}\Omega$ $V_2 = V_{DM} = 600\text{ V}$; $R_L = 3\text{ k}\Omega$ $V_2 = V_{DM} = 700\text{ V}$; $R_L = 3\text{ k}\Omega$ $V_2 = V_{DM} = 800\text{ V}$; $R_L = 3\text{ k}\Omega$ </div> <div style="width: 15%; text-align: right;"> 2N682 2N683 2N685 2N686 2N687 2N688 2N689 2N690 2N691 2N692 2N5206 </div> </div>	V_{GT2}	.25		V
Reverse blocking current ($T_C = -65\text{ }^\circ\text{C}$) AC method, bias condition D; $f = 60\text{ Hz}$; $V_{RRM} = \text{rated}$	I_{RRM3}		2	mA (pk)
Forward blocking current ($T_C = -65\text{ }^\circ\text{C}$) AC method, bias condition D; $f = 60\text{ Hz}$; $V_{DRM} = \text{rated}$	I_{DRM3}		2	mA (pk)
Gate trigger voltage and current ($T_C = -65\text{ }^\circ\text{C}$) $V_2 = V_D = 6\text{ V}$; $R_L = 50\text{ }\Omega$; $R_e = 20\text{ }\Omega$ maximum	V_{GT3} I_{GT2}		3 80	V mA
Exponential rate of voltage rise Bias condition D; $T_C = +120\text{ }^\circ\text{C}$ minimum, $dv/dt = 25\text{ v}/\mu\text{s}$; repetition rate = 60 pps; test duration = 15 s; $C = 1.0\text{ }\mu\text{F}$; $R_L = 50\text{ }\Omega$ <div style="display: flex; justify-content: space-between;"> <div style="width: 80%;"> $V_{AA} = 50\text{ V}$ $V_{AA} = 100\text{ V}$ $V_{AA} = 200\text{ V}$ $V_{AA} = 250\text{ V}$ $V_{AA} = 300\text{ V}$ $V_{AA} = 400\text{ V}$ $V_{AA} = 500\text{ V}$ $V_{AA} = 600\text{ V}$ $V_{AA} = 700\text{ V}$ $V_{AA} = 800\text{ V}$ $V_{AA} = 1,000\text{ V}$ </div> <div style="width: 15%; text-align: right;"> 2N682 2N683 2N685 2N686 2N687 2N688 2N689 2N690 2N691 2N692 2N5206 </div> </div>	V_D	47 95 190 240 285 380 475 570 665 760 950		V

ELECTRICAL CHARACTERISTICS (continued)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Circuit-commutated turn-off time $T_C = +120^\circ\text{C}$ minimum; $I_{TM} = 10\text{ A}$; $t_{on} = 100 \pm 50\ \mu\text{s}$; $di/dt = 5\text{ A}/\mu\text{s}$ minimum; $di/dt = 8\text{ A}/\mu\text{s}$ maximum; reverse voltage at $t_1 = 15\text{ V}$ minimum; repetition rate = 60 pps maximum; $di/dt = 20\text{ V}/\mu\text{s}$; gate bias conditions; gate source voltage = 0 V; gate source resistance = 100 Ω	t_{off}			
$V_{DM} = V_{DRM} = 50\text{ V (pk)}$; $V_{RRM} = 50\text{ V maximum}$ 2N682		30	μs	
$V_{DM} = V_{DRM} = 100\text{ V (pk)}$; $V_{RRM} = 100\text{ V maximum}$ 2N683		30		
$V_{DM} = V_{DRM} = 200\text{ V (pk)}$; $V_{RRM} = 200\text{ V maximum}$ 2N685		30		
$V_{DM} = V_{DRM} = 250\text{ V (pk)}$; $V_{RRM} = 250\text{ V maximum}$ 2N686		30		
$V_{DM} = V_{DRM} = 300\text{ V (pk)}$; $V_{RRM} = 300\text{ V maximum}$ 2N687		30		
$V_{DM} = V_{DRM} = 400\text{ V (pk)}$; $V_{RRM} = 400\text{ V maximum}$ 2N688		30		
$V_{DM} = V_{DRM} = 500\text{ V (pk)}$; $V_{RRM} = 500\text{ V maximum}$ 2N689		40		
$V_{DM} = V_{DRM} = 600\text{ V (pk)}$; $V_{RRM} = 600\text{ V maximum}$ 2N690		40		
$V_{DM} = V_{DRM} = 700\text{ V (pk)}$; $V_{RRM} = 700\text{ V maximum}$ 2N691		60		
$V_{DM} = V_{DRM} = 800\text{ V (pk)}$; $V_{RRM} = 800\text{ V maximum}$ 2N692		60		
$V_{DM} = V_{DRM} = 1,000\text{ V (pk)}$; $V_{RRM} = 1,000\text{ V max.}$ 2N5206	60			
Gate controlled turn-on time $V_{AA} = 50\text{ V}$ for 2N682 2N682, $V_{AA} = 100\text{ V}$ for 2N683, 2N685 through 2N692 2N683, and 2N5206 2N685 $I_{TM} = 10\text{ A}$; $V_{GG} = 10\text{ V}$; $R_e = 25\ \Omega$ through $t_{p1} = 15 \pm 5\ \mu\text{s}$; $4\text{ A}/\mu\text{s} \leq di/dt \leq 200\text{ A}/\mu\text{s}$. 2N692 and 2N5206	t_{on}		5	μs

PACKAGE DIMENSIONS

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Device contour, except on hex head and noted terminal dimensions, is optional within zone defined by CD and OAH, CD not to exceed actual HF.
3. Contour and angular orientation of terminals 1 and 2 with respect to hex portion and to each other are optional.
4. Chamfer or undercut on one or both ends of the hexagonal portion are optional.
5. Square or radius on end of terminal is optional.
6. Minimum difference in terminal lengths to establish datum line for numbering terminals.
7. Dimension SD is pitch diameter of coated threads.
8. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.

Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
b	.115	.139	2.92	3.53	3
b1	.210	.300	5.33	7.62	3
CD		.543		13.8	2
CH		.550		14.00	
e2	.125		3.17		6
HF	.544	.563	13.8	14.3	
HT	.075	.200	1.9	5.08	4
OAH		1.193		30.3	2
S	.120		3.05		3
SD	¼ - 28 UNF 2A				
SL	.422	.453	10.7	11.5	
SU		.090		2.29	
ΦT	.125	.165	3.17	4.19	
ΦT1	.060	.075	1.52	1.9	
UD	.220	.249	5.59	6.32	

Terminal 1	Gate	
Terminal 2	Cathode	5
Terminal 3	Anode (Stud)	7